FCB120S10D1

*e*SiC Silicon Carbide Schottky Diode

1200V, 10A

Description

The 1200V *e*SiC is an advanced Faster Semiconductor's silicon carbide diode family. This technology combines the benefits of excellent low forward voltage and robustness. Consequently, the *e*SiC family is suitable for application requiring high power efficiency.

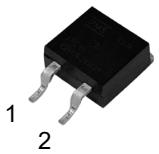
Features

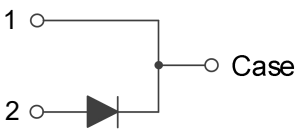
V_{RRM}	I_F	$T_{J,max}$	Q_C
1200 V	10 A	175 ℃	63 nC

- No reverse recovery current
- Low forward voltage
- 175°C Max junction temperature
- High surge current capability
- Switching behavior independent of temperature
- Pb-Free, Halogen Free and RoHS compliant

Applications

- Solar inverter, UPS
- EV charging station
- Power Factor Correction





Absolute Maximum Ratings (T_C = 25℃ unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage		1200	V
I_F	Forward Current	T_C=154℃	10	A
$I_{F,SM}$	Non-Repetitive Forward Surge Current	T_C=25℃, t_p=10ms	79	A
		T_C=150℃, t_p=10ms	67	A
$I_{F,Max}$	Non-Repetitive Peak Forward Current	T_C=25℃, t_p=10us	810	A
		T_C=150℃, t_p=10us	690	A
I^2dt value	$\int I^2t$	T_C=25℃, t_p=10ms	31	A^2S
		T_C=150℃, t_p=10ms	23	A^2S
P_{tot}	Power Dissipation	T_C=25C	167	W
T_J,T_{STG}	Operating Junction and Storage Temperature		-55 to +175	℃

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.9	℃/W

Package Marking and Ordering Information

Part Number	Top Marking	Package	Packing Method	Quantity
FCB120S10D1	FCB120S10D1	TO-263	Tape & Reel	2500 units

Electrical Characteristics (T_C = 25℃ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_F	Forward Voltage	I_F=10A, T_C=25℃		1.39	1.70	V
		I_F=10A, T_C=175℃		1.8	-	
I_R	Reverse Current	V_R=1200V, T_C=25℃		-	100	μA
		V_R=1200V, T_C=175℃		-	300	
Q_C	Total Capacitive Charge	V_R=800V, T_C=25℃		63		nC
C	Total Capacitance	V_R=1V, f=100Khz		696		pF
		V_R=800V, f=100Khz		44		
E_C	Capacitance Stored Energy	V_R=800V, T_C=25℃		18		μJ

Typical Performance Characteristics

Figure 1. Power Derating

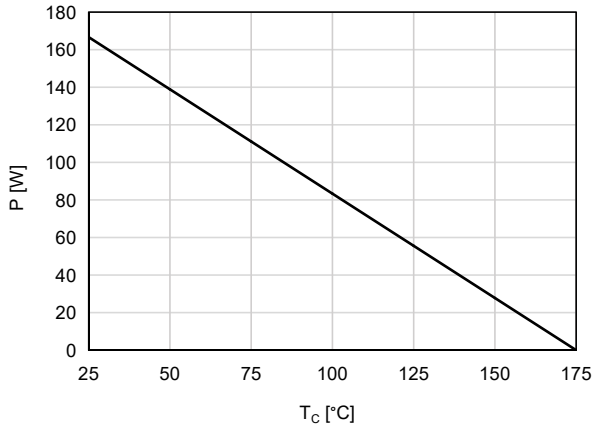


Figure 2. Current Derating

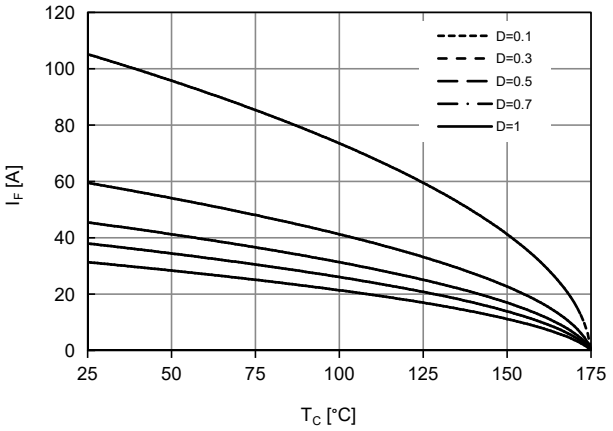


Figure 3. Forward Characteristics

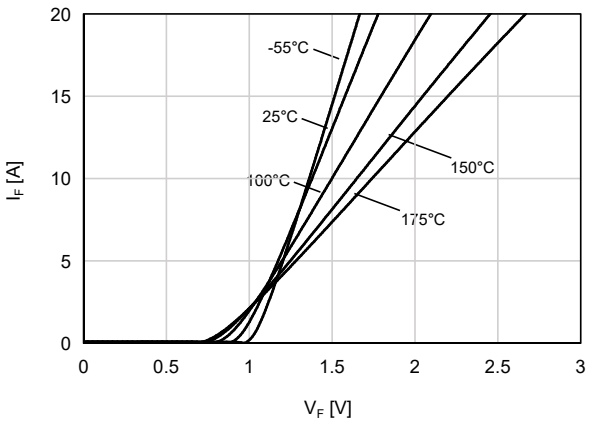


Figure 4. Reverse Characteristics

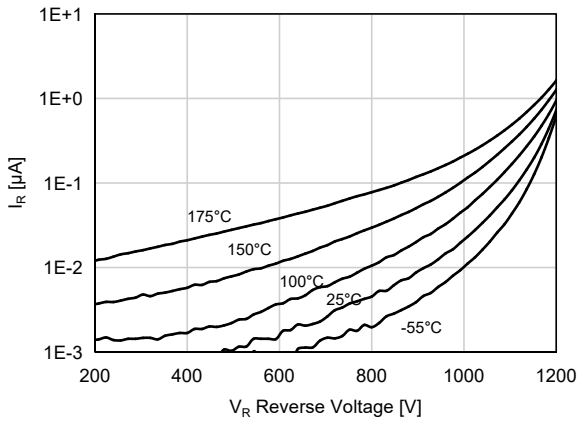


Figure 5. Capacitive Charge Characteristic

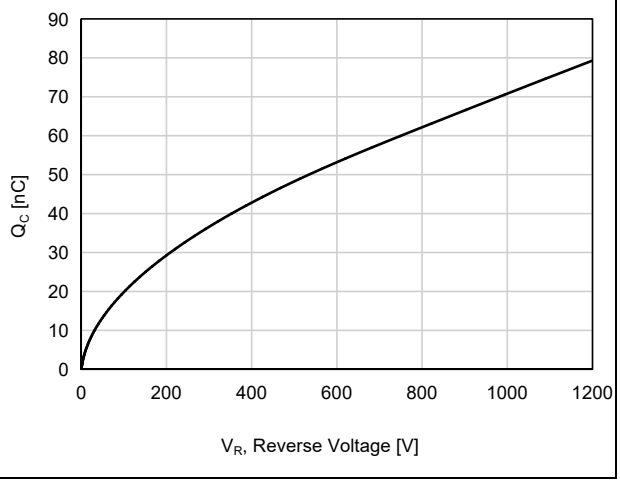
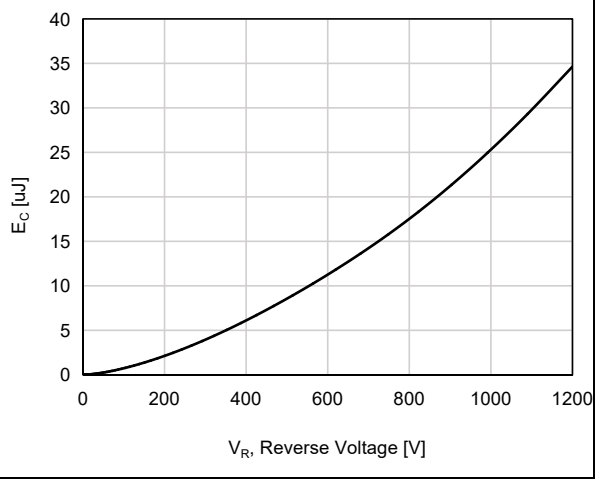


Figure 6. Capacitance Stored Energy



Typical Performance Characteristics

Figure 7. Capacitance Characteristic

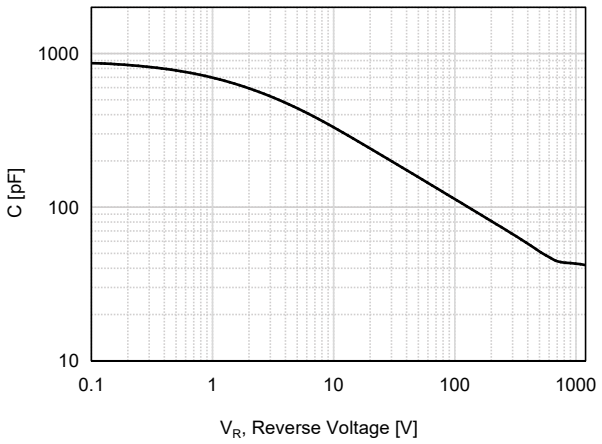
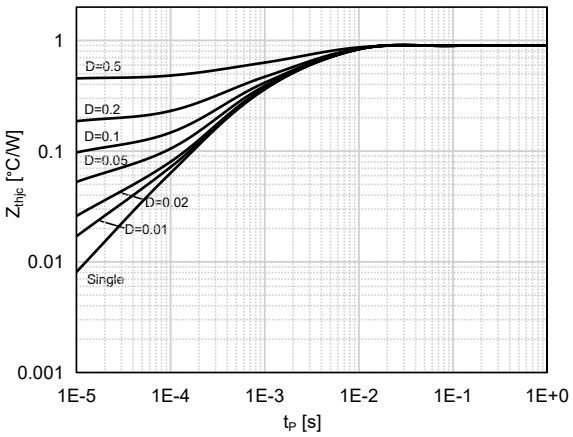
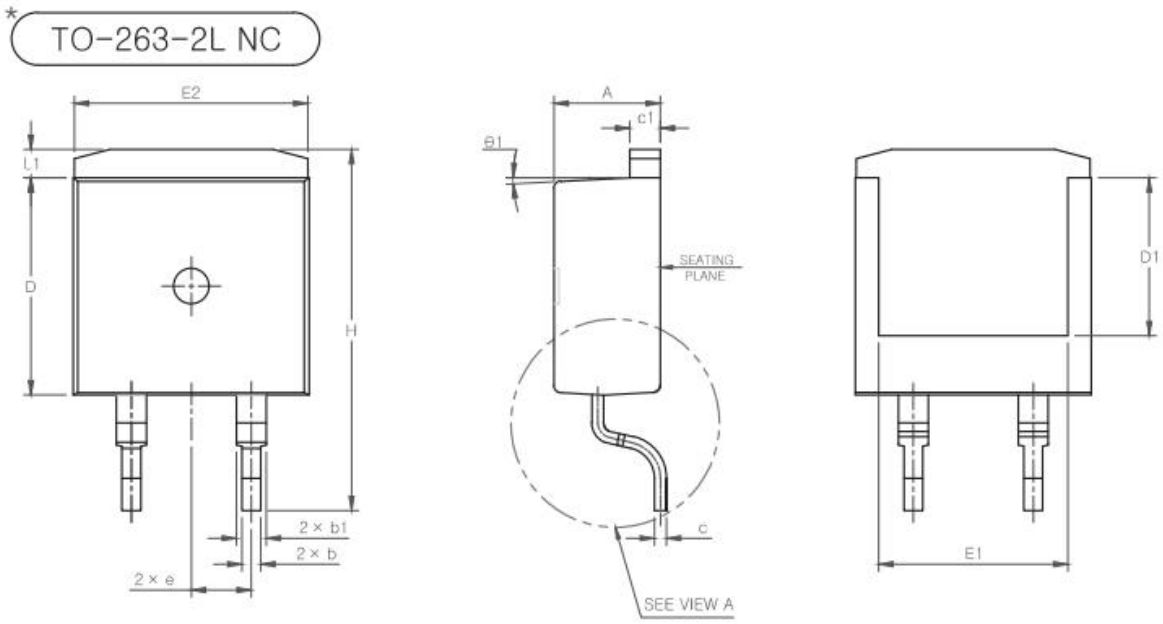


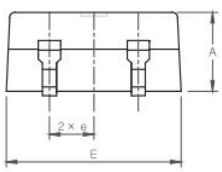
Figure 8. Transient Thermal Response Curve

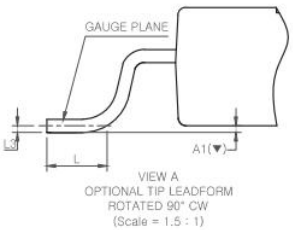


Package Outlines

TO-263-2L







NOTE

1. THESE DIMENSIONS DO NOT INCLUDE PROTRUSIONS OF THE MOLD.
2. THE "( )" MARK IS THE REFERENCE
3. COPLANARITY : MAX 0.10mm

SYMBOL	MIN	NOM	MAX
A	4.30	4.50	4.70
A1(▼)	0.00	-	0.25
b	0.70	0.80	0.90
b1	1.17	1.27	1.37
c	0.45	0.50	0.60
c1	1.25	1.30	1.40
D	9.00	9.20	9.40
D1	6.50	6.70	6.90
E	9.80	10.00	10.20
E1	7.80	8.00	8.20
E2	9.70	9.90	10.10
e		2.54 BSC	
H	15.00	15.30	15.60
L	2.00	2.30	2.60
L1	1.00	1.20	1.40
L3		0.254 BSC	
θ1		(3°)	

* Dimensions in millimeters